



PRESS RELEASE

16Mbit Flash Memory accesses at 70ns

EON Silicon Solution's EN29LV160 is a 16Mbit erasable, read/write non-volatile flash memory. Available from exclusive distributor Focus EDL, the new device is organized as 2M by 8 or 16M by 1.

The EN29LV160 features single 3.0V operation to minimize system level power requirements, whilst access times as fast as 70ns eliminate the need for WAIT states in high performance microprocessor systems. Power consumption at 5MHz is typically 20mA in program/erase mode, 9mA in active read mode and less than 1 μ A in standby.

The new memory is designed to allow single sector (500ms typical) or full chip erase (17.5s typical) operation. Any byte can typically be programmed in just 8 μ s. The device can sustain a minimum of 1,000,000 program/erase cycles on each sector.

Fabricated using triple-metal, double-poly, triple-well CMOS technology, packaging options are 48-pin TSOP or 48 ball 6mm x 8mm FBGA and both commercial and industrial temperature rated devices are available.